

S-35730 Series

FOR AUTOMOTIVE 125°C OPERATION CLOCK PULSE OUTPUT WITH FREQUENCY SETTING PIN CONVENIENCE TIMER

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Rev.1.0 00

The convenience timer is a CMOS timer IC which operates with low current consumption, and is suitable for the time management of the relative time.

The S-35730 Series outputs the clock pulse.

4 types of clock pulse frequency can be selected from 1 Hz to 32.768 kHz depending on the SET0 pin and the SET1 pin settings.

Caution This product can be used in vehicle equipment and in-vehicle equipment. Before using the product in the purpose, contact to SII Semiconductor Corporation is indispensable.

■ Features

Clock pulse output function: Settable clock pulse frequency, with an output control pin

• Low current consumption: 0.7 μ A typ. (Crystal oscillator: $C_L = 6.0$ pF, $V_{DD} = 3.0$ V, ENBL pin = "H", Ta = +25°C,

FOUT pin = Nch open-drain output)

• Wide range of operation voltage: 1.8 V to 5.5 V

• Built-in 32.768 kHz crystal oscillation circuit

• Operation temperature range: Ta = -40°C to +125°C

• Lead-free (Sn 100%), halogen-free

AEC-Q100 in process*1

*1. Contact our sales office for details.

■ Applications

- · Intermittent operation of various systems
- Regular status monitoring of various systems

■ Package

• TMSOP-8

■ Block Diagram

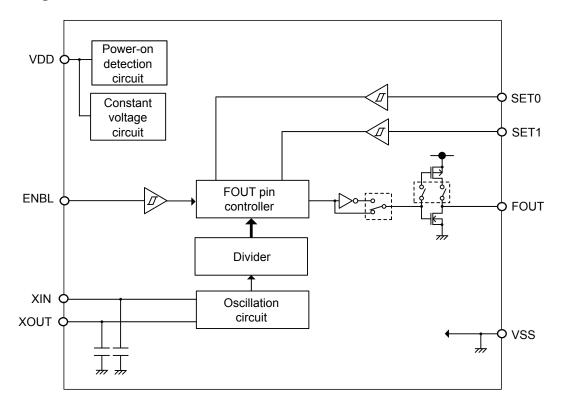


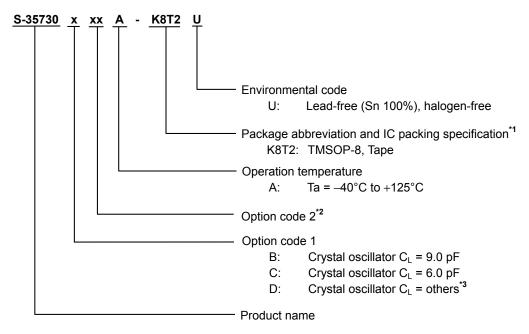
Figure 1

■ AEC-Q100 in Process

Contact our sales office for details of AEC-Q100 reliability specification.

■ Product Name Structure

1. Product name



- *1. Refer to the tape drawing.
- *2. A sequence number added by the optional function that is user-selected.
- *3. Contact our sales office for details.

2. Package

Table 1 Package Drawing Codes

Package Name	Dimension	Tape	Reel
TMSOP-8	FM008-A-P-SD	FM008-A-C-SD	FM008-A-R-SD

3. Product name list

Table 2

Droduct Name	FOLIT Din Output Form*1	SET0 Pin, SET1 Pin Settings*2 (SET0, SET1)			
Product Name	FOUT Pin Output Form 1	0, 0	0, 1	1, 0	1, 1
S-35730C01A-K8T2U	CMOS output	32.768 kHz	32 Hz	1.024 kHz	1 Hz

^{*1.} The pin of Nch open-drain output / CMOS output is selectable. Refer to "■ Pin Functions".

Remark Please contact our sales office for products with specifications other than the above.

^{*2.} Regarding the pin settings and clock pulse frequency combinations, refer to "■ FOUT Pin Clock Pulse Output".

■ Pin Configuration

1. TMSOP-8

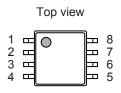


Figure 2

Table 3 List of Pins

Pin No.	Symbol	Description	I/O	Configuration
1	ENBL	Input pin for clock pulse output control	Input	CMOS input
2	XOUT	Connection pins for		
3	XIN	crystal oscillator	_	_
4	VSS	GND pin	_	
5	FOUT	Output pin for clock pulse	Output	Nch open-drain output / CMOS output is selectable
6	SET0	Input pins for clock pulse	lanut	01400
7	SET1	frequency setting	Input	CMOS input
8	VDD	Pin for positive power supply	_	_

■ Pin Functions

1. SET0, SET1 (Input for clock pulse frequency setting) pins

These pins input the clock pulse frequency setting signals.

4 types of clock pulse frequency can be selected depending on the pin settings. Regarding the combination, refer to "1. Options of clock pulse frequency" in "■ FOUT Pin Clock Pulse Output".

2. ENBL (Input for clock pulse output control) pin

This pin controls the clock pulse output from the FOUT pin. The clock pulse is output from the FOUT pin when the ENBL pin is "H". The FOUT pin is fixed when the ENBL pin is "L".

3. FOUT (Output for clock pulse) pin

This pin outputs the clock pulse. Regarding the operation of the clock pulse output, refer to "2. ENBL pin and clock pulse output of FOUT pin " in "■ FOUT Pin Clock Pulse Output".

Also, the FOUT pin output form of Nch open-drain output / CMOS output can be selected.

4. XIN, XOUT (Connection for crystal oscillator) pins

Connect a crystal oscillator between the XIN pin and the XOUT pin.

5. VDD (Positive power supply) pin

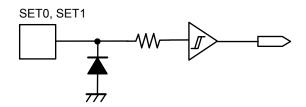
Connect this pin with a positive power supply. Regarding the values of voltage to be applied, refer to "

Recommended Operation Conditions".

6. VSS pin

Connect this pin to GND.

■ Equivalent Circuits of Pins



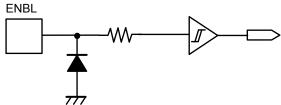
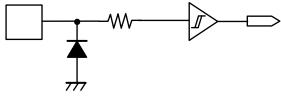


Figure 3 SET0 Pin, SET1 Pin



FOUT

Figure 4 ENBL Pin

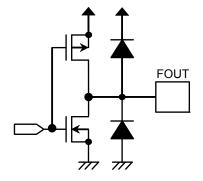


Figure 5 FOUT Pin (Nch Open-drain Output)

Figure 6 FOUT Pin (CMOS Output)

■ Absolute Maximum Ratings

Table 4

Item	Symbol	Applied Pin	Absolute Maximum Rating	Unit
Power supply voltage	V_{DD}	_	$V_{SS} - 0.3$ to $V_{SS} + 6.5$	V
Input voltage	V _{IN}	SET0, SET1, ENBL	$V_{SS} - 0.3$ to $V_{SS} + 6.5$	V
Output voltage	Vout	FOUT*1	$V_{SS} - 0.3$ to $V_{SS} + 6.5$	V
	VOUT	FOUT*2	$V_{SS} - 0.3 \text{ to } V_{DD} + 0.3 \le V_{SS} + 6.5$	V
Operation ambient temperature*3	T _{opr}	_	-40 to +125	°C
Storage temperature	T _{stg}	_	−55 to +150	°C

^{*1.} When Nch open-drain output is selected.

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ Recommended Operation Conditions

Table 5

 $(V_{SS} = 0 V)$

						1 00 - /
Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Operation power supply voltage	V_{DD}	Ta = -40°C to +125°C	1.8	_	5.5	V

■ Oscillation Characteristics

Table 6

(Ta = +25°C, V_{DD} = 3.0 V, V_{SS} = 0 V unless otherwise specified)

(Crystal oscillator (NX3215SA, C_L = 6.0 pF) manufactured by Nihon Dempa Kogyo Co., Ltd.)

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Oscillation start voltage	V _{STA}	Within 10 seconds	1.8	1	5.5	V
Oscillation start time	t _{STA}	_	_	I	1	s
IC-to-IC frequency deviation*1	δΙC	_	-20	1	+20	ppm

^{*1.} Reference value

^{*2.} When CMOS output is selected.

^{*3.} Conditions with no condensation or frost. Condensation or frost causes short-circuiting between pins, resulting in a malfunction.

■ DC Electrical Characteristics

Table 7

(Ta = -40°C to +125°C, V_{SS} = 0 V unless otherwise specified)

(Crystal oscillator (NX3215SA, $C_L = 6.0 \text{ pF}$) manufactured by Nihon Dempa Kogyo Co., Ltd.)

Item	Symbol	Applied Pin	Condition	Min.	Тур.	Max.	Unit
Current consumption 1	I _{DD1}	_	V_{DD} = 3.0 V, Ta = -40°C to +85°C, ENBL pin = V_{SS} , FOUT pin = no load	_	1.7	3.0	μΑ
Consumption 1			V_{DD} = 3.0 V, Ta = +125°C, ENBL pin = V_{SS} , FOUT pin = no load	-	2.7	4.5	μΑ
			V_{DD} = 3.0 V, Ta = -40°C to +85°C, ENBL pin = V_{DD} , FOUT pin output = 32.768 kHz, FOUT pin = no load*1	Г	0.7	0.85	μΑ
Current			V_{DD} = 3.0 V, Ta = +125°C, ENBL pin = V_{DD} , FOUT pin output = 32.768 kHz, FOUT pin = no load*1	-	1.2	1.9	μΑ
consumption 2	I _{DD2}	_	V_{DD} = 3.0 V, Ta = -40°C to +85°C, ENBL pin = V_{DD} , FOUT pin output = 32.768 kHz, FOUT pin = no load*2	-	4.0	6.0	μΑ
			V_{DD} = 3.0 V, Ta = +125°C, ENBL pin = V_{DD} , FOUT pin output = 32.768 kHz, FOUT pin = no load*2	-	4.5	7.0	μΑ
High level input leakage current	I _{IZH}	SET0, SET1, ENBL	$V_{IN} = V_{DD}$	-0.5	ı	0.5	μΑ
Low level input leakage current	I _{IZL}	SET0, SET1, ENBL	V _{IN} = V _{SS}	-0.5	-	0.5	μА
High level output leakage current	I _{OZH}	FOUT*2	$V_{OUT} = V_{DD}$	-0.5	ı	0.5	μΑ
Low level output leakage current	I _{OZL}	FOUT*2	$V_{OUT} = V_{SS}$	-0.5	_	0.5	μΑ
High level input voltage	V _{IH}	SET0, SET1, ENBL	_	$0.7 \times V_{DD}$	-	V _{SS} + 5.5	V
Low level input voltage	V _{IL}	SET0, SET1, ENBL	_	V _{SS} - 0.3	_	$0.3 \times V_{DD}$	V
High level output voltage*2	V _{OH}	FOUT	I _{OH} = -0.4 mA	$0.8 \times V_{DD}$	-	_	V
Low level output voltage	V _{OL}	FOUT	I _{OL} = 2.0 mA	_	_	0.4	V

^{*1.} When Nch open-drain output is selected.

^{*2.} When CMOS output is selected.

■ FOUT Pin Clock Pulse Output

1. Options of clock pulse frequency

4 types of FOUT pin clock pulse output can be selected as the option from the frequency of 1 Hz to 32.768 kHz. **Table 8** shows the pin settings and the list of options for the FOUT pin clock pulse frequency.

Pin S	etting	Clock Pulse	Clock Pulse	Clock Pulse	Clock Pulse
SET0	SET1	Frequency 1	Frequency 2	Frequency 3	Frequency 4
L	L	32.768 kHz	16.384 kHz	8.192 kHz	4.096 kHz
L	Н	128 Hz	64 Hz	32 Hz	16 Hz
Н	L	2.048 kHz	1.024 kHz	512 Hz	256 Hz
Н	Н	8 Hz	4 Hz	2 Hz	1 Hz

Table 8 List of Options

For example, when the pin setting is SET0 pin = "L" and SET1 pin = "L", 1 clock pulse frequency can be selected from "32.768 kHz", "16.384 kHz", "8.192 kHz" and "4.096 kHz". The others cannot be selected.

Table 9 shows the example of the clock pulse frequency combination.

		•
Pin Setting		Clock Bulge Frequency
SET0	SET1	Clock Pulse Frequency
L	L	32.768 kHz
L	Н	32 Hz
Н	L	1.024 kHz
Н	Н	1 Hz

Table 9 Example of Options

2. ENBL pin and clock pulse output of FOUT pin

The FOUT pin outputs the clock pulse when the ENBL pin is "H". The FOUT pin is fixed to Nch open-drain output = "H" or CMOS output = "L" when the ENBL pin is "L". Since the input signal of the ENBL pin is not synchronized with the clock pulse output from the FOUT pin, the duty ratio may change when the "H" and "L" of the ENBL pin changes. The example of the FOUT pin output timing is shown below.

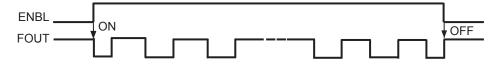


Figure 7 Example FOUT Pin Output Timing (Nch Open-drain Output)



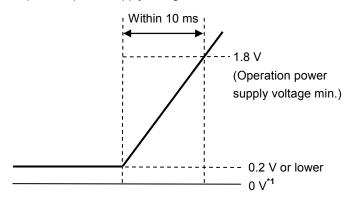
Figure 8 Example of FOUT Pin Output Timing (CMOS Output)

The SET0 pin and the SET1 pin input signals are not synchronized with the clock pulse output from the FOUT pin as well. Therefore, duty ratio may change if the SET0 pin and the SET1 pin settings are changed when the ENBL pin is "H".

Moreover, since the crystal oscillation circuit is unstable immediately after power-on, regardless of the status of the ENBL pin, the FOUT pin is fixed to Nch open-drain output = "H" or CMOS output = "L" for about 0.5 seconds after power-on.

■ Power-on Detection Circuit

In order for the power-on detection circuit to operate normally, raise the power supply voltage of the IC from 0.2 V or lower so that it reaches 1.8 V of the operation power supply voltage minimum value within 10 ms, as shown in **Figure 9**.



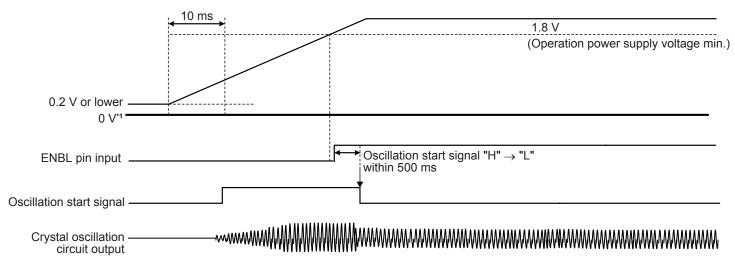
*1. 0 V means that there is no potential difference between the VDD pin and the VSS pin of the S-35730 Series.

Figure 9 How to Raise Power Supply Voltage

If the power supply voltage of the S-35730 Series cannot be raised under the above conditions, the power-on detection circuit may not operate normally and an oscillation may not start. In such case, perform the operations shown in "1. When power supply voltage is raised at ENBL pin = "L" " and "2. When power supply voltage is raised at ENBL pin = "H" ".

1. When power supply voltage is raised at ENBL pin = "L"

Set the ENBL pin to "L" until the power supply voltage reaches 1.8 V or higher. While the ENBL pin is set to "L", the oscillation start signal becomes "H", and the crystal oscillation circuit normally oscillates. If the ENBL pin is set to "H" after the power supply voltage reaches 1.8 V, the oscillation start signal becomes "L" within 500 ms, and the oscillation status is maintained.

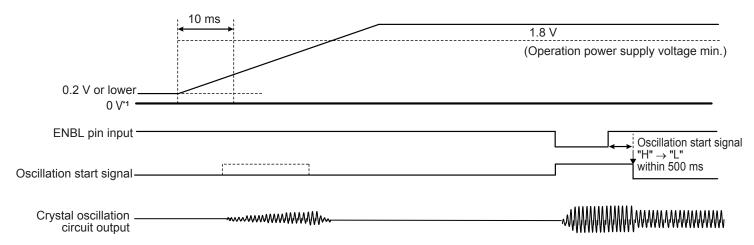


*1. 0 V means that there is no potential difference between the VDD pin and the VSS pin of the S-35730 Series.

Figure 10 When Power Supply Voltage is Raised at ENBL Pin = "L"

2. When power supply voltage is raised at ENBL pin = "H"

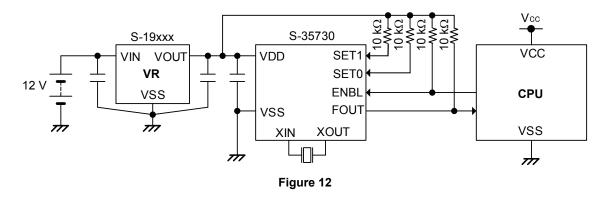
Set the ENBL pin to "L" after the power supply voltage reaches 1.8 V or higher. If the ENBL pin is set to "L" for 500 ms or longer, the oscillation start signal becomes "H", and the crystal oscillation circuit normally oscillates. After that, if the ENBL pin is set to "H", the oscillation start signal becomes "L" within 500 ms, and the oscillation status is maintained.



*1. 0 V means that there is no potential difference between the VDD pin and the VSS pin of the S-35730 Series.

Figure 11 When Power Supply Voltage is Raised at ENBL Pin = "H"

■ Example of Application Circuit



Caution The above connection diagram does not guarantee operation. Set the constants after performing sufficient evaluation using the actual application

■ Configuration of Crystal Oscillation Circuit

Since the S-35730 Series has built-in capacitors (C_g and C_d), adjustment of oscillation frequency is unnecessary. However, the crystal oscillation circuit is sensitive to external noise and parasitic capacitance (C_P), these effects may become a factor to worsen the clock accuracy. Therefore, the following steps are recommended for optimizing the configuration of the crystal oscillation circuit.

- Locate the bypass capacitor adjacent to the power supply pin of the S-35730 Series.
- Place the S-35730 Series and the crystal oscillator as close to each other as possible, and shorten the wiring.
- Increase the insulation resistance between pins and the board wiring patterns of XIN and XOUT.
- Do not place any signal or power lines close to the crystal oscillation circuit.
- Locate the GND layer immediately below the crystal oscillation circuit.
 (In the case of a multi-layer board, only the layer farthest from the oscillation circuit should be located as the GND layer.
 Do not locate a circuit pattern on the intermediate layers.)

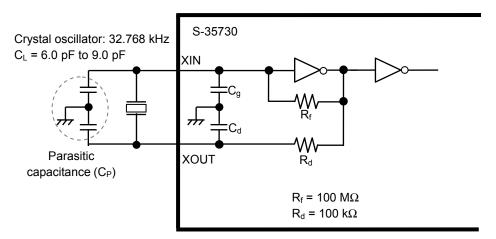


Figure 13 Configuration of Crystal Oscillation Circuit

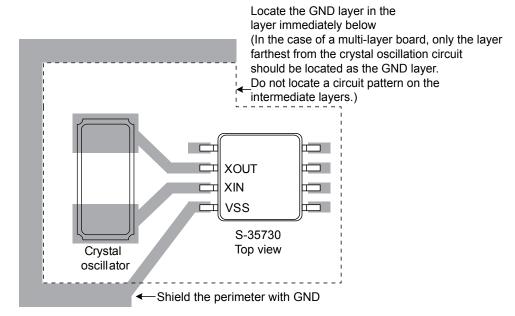


Figure 14 Example of Recommended Connection Pattern Diagram

- Caution 1. Oscillation characteristics are subject to the variation of each component such as board parasitic capacitance, parasitic resistance, crystal oscillator and external capacitor. When configuring the crystal oscillation circuit, pay sufficient attention for them.
 - 2. When using the product in automobile equipment, select the components which can be automobile carried for each component such as crystal oscillator, external capacitor and board.

■ Cautions When Using Crystal Oscillator

Request a crystal oscillator maker for a matching assessment of the IC and the crystal oscillator. Refer to **Table 10** for recommended crystal oscillator characteristics values. When using the product in an environment over $Ta = +85^{\circ}C$, it is recommended to ensure the oscillation allowance shown in **Table 10** at room temperature.

Table 10 Crystal Oscillator Characteristics

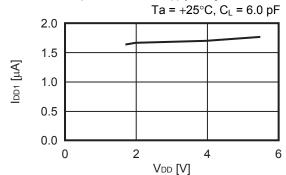
Crystal Oscillator C _L Value (Load Capacitance)	R ₁ Value (Equivalent Series Resistance)	Oscillation Allowance at Power-on
9.0 pF	80 k Ω max.	5 times or more
6.0 pF	80 kΩ max.	5 times or more

■ Precautions

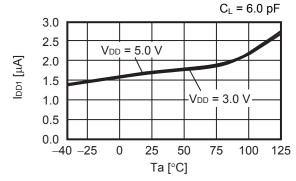
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
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■ Characteristics (Typical Data)

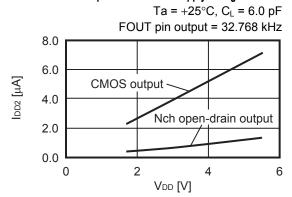
1. Current consumption 1 vs. Power supply voltage characteristics



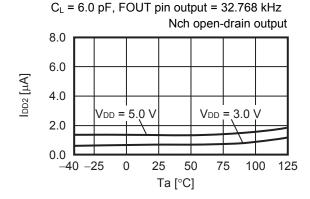
2. Current consumption 1 vs. Temperature characteristics



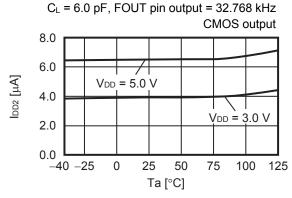
3. Current consumption 2 vs. Power supply voltage characteristics



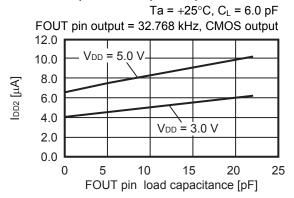
4. Current consumption 2 vs. Temperature characteristics



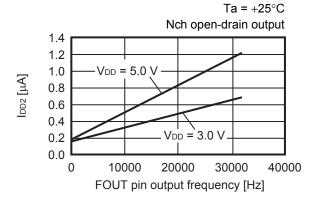
5. Current consumption 2 vs. Temperature characteristics



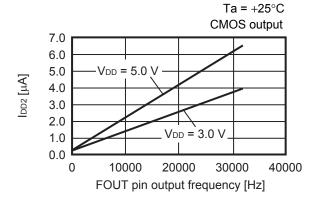
6. Current consumption 2 vs. FOUT pin load capacitance characteristics



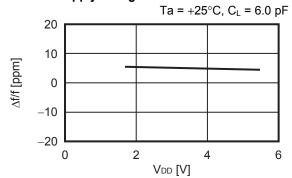
7. Current consumption 2 vs. FOUT pin output frequency characteristics



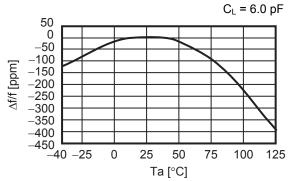
8. Current consumption 2 vs. FOUT pin output frequency characteristics



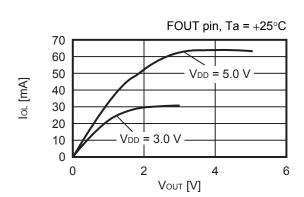
9. Crystal oscillator frequency deviation vs. Power supply voltage characteristics



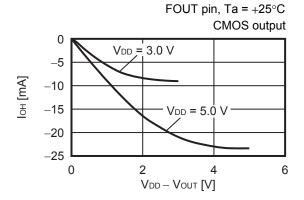
10. Crystal oscillator frequency deviation vs. Temperature characteristics

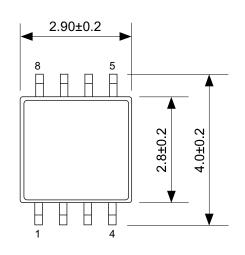


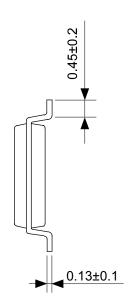
11. Low level output current vs. Output voltage characteristics

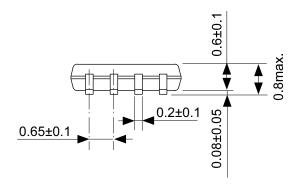


12. High level output current vs. V_{DD} – V_{OUT} characteristics



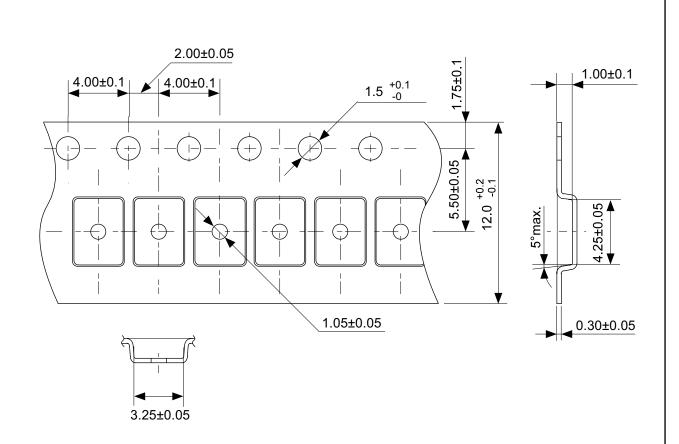


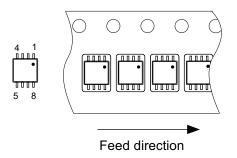




No. FM008-A-P-SD-1.2

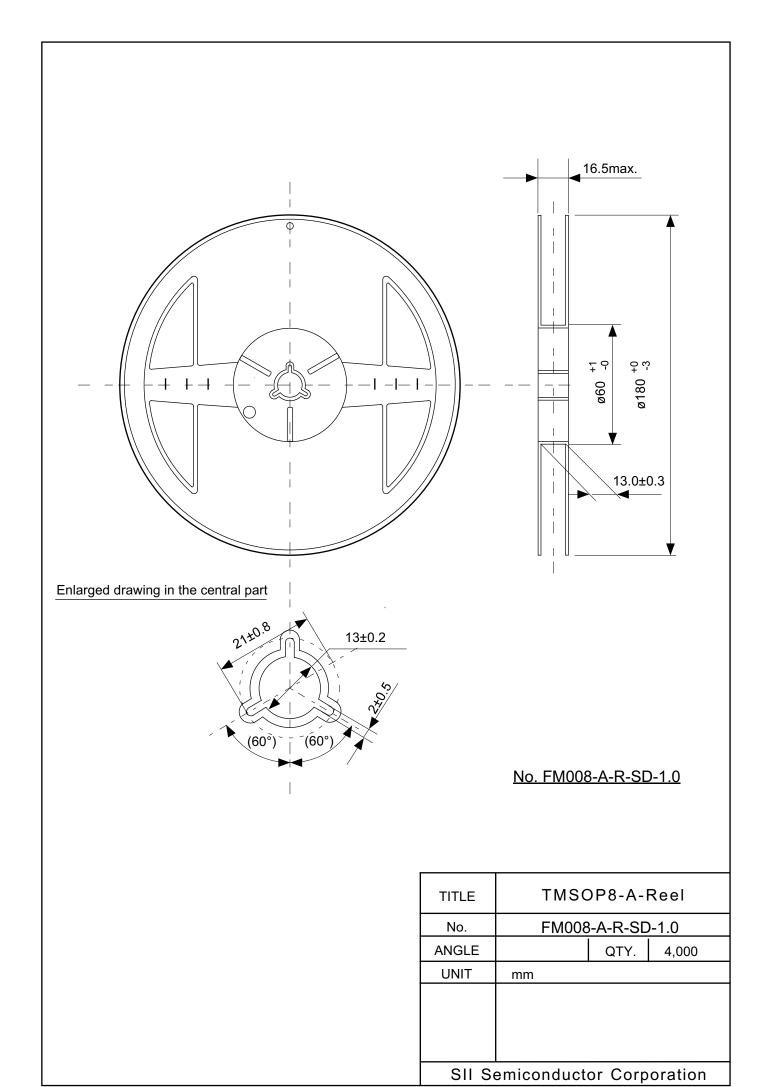
TITLE	TMSOP8-A-PKG Dimensions	
No.	FM008-A-P-SD-1.2	
ANGLE	\$	
UNIT	mm	
SII Semiconductor Corporation		





No. FM008-A-C-SD-2.0

TITLE	TMSOP8-A-Carrier Tape		
No.	FM008-A-C-SD-2.0		
ANGLE			
UNIT	mm		
SII Semiconductor Corporation			



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